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May 3, 2002

To: Commissioner of Patents and Trademarks  
Washington, D.C. 20231

Fr: George O. Saile, Reg. No. 19,572  
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Poughkeepsie, N.Y. 12603

Subject:

Serial No. 10/086,258 03/04/02

Ming-Hwa Yoo, Shih-Chi Lin,  
Yi-Lung Cheng, Szu-An Wu,  
Ying-Lang Wang

A NOVEL METHOD TO SOLVE IMD-FSG  
PARTICLE AND INCREASE Cp YIELD BY  
USING A NEW TOUGHER UFUN SEASON FILM

Grp. Art Unit: 1763

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TC 1700

#### INFORMATION DISCLOSURE STATEMENT

Enclosed is Form PTO-1449, Information Disclosure Citation  
In An Application.

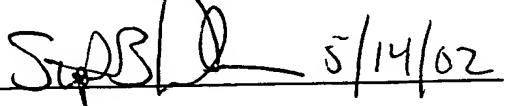
The following Patents and/or Publications are submitted to  
comply with the duty of disclosure under CFR 1.97-1.99 and  
37 CFR 1.56. Copies of each document is included herewith.

#### CERTIFICATE OF MAILING

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Trademarks, Washington, D.C. 20231, on May 14, 2002.

Stephen B. Ackerman, Reg.# 37761

Signature/Date

 5/14/02

U.S. Patent 5,983,906 to Zhao et al., "Methods and Apparatus for a Cleaning Process in a High Temperature, Corrosive, Plasma Environment," describes systems, methods and apparatus for depositing titanium films at rates of up to 200 Å/minute on semiconductor substrates from a titanium tetrachloride source.

U.S. Patent 6,020,035 to Gupta et al., "Film to Tie Up Loose Fluorine in the Chamber After a Clean Process," describes an undoped silicate glass (USG) seasoning film and process.

U.S. Patent 5,811,356 to Murugesh et al., "Reduction in Mobile Ion and Metal Contamination by Varying Season Time and Bias RF Power During Chamber Cleaning," describes a method and apparatus for reducing the concentration of mobile ion and metal contaminants in a processing chamber.

U.S. Patent 6,121,161 to Rossman et al., "Reduction of Mobile Ion and Metal Contamination in HDP-CVD Chambers Using Chamber Seasoning Film Depositions," describes a method and apparatus for controlling the introduction of contaminates into a deposition chamber that occur naturally within the chamber components.

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U.S. Patent 6,136,211 to Qian et al., "Self-Cleaning Etch Process," describes a self-cleaning etch process whereby during etching of a substrate in an etching chamber, a thin non-homogeneous etch residue deposited on the surfaces of the walls and components of the etching chamber are simultaneously cleaned.

U.S. Patent 5,705,080 to Leung et al., "Plasma-Inert Cover and Plasma Cleaning Process," describes a plasma-inert cover and plasma cleaning process.

Sincerely,  


Stephen B. Ackerman,  
Reg. No. 37761

